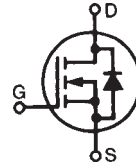


TrenchT2™ Power MOSFETs

IXTA80N12T2 IXTP80N12T2

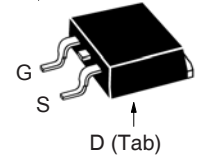
$$\begin{aligned} V_{DSS} &= 120V \\ I_{D25} &= 80A \\ R_{DS(on)} &\leq 17m\Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier

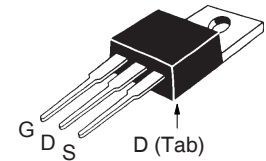


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	120	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$	120	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	80	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	200	A
I_A	$T_C = 25^\circ\text{C}$	40	A
E_{AS}	$T_C = 25^\circ\text{C}$	400	mJ
P_D	$T_C = 25^\circ\text{C}$	325	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263AA (IXTA)



TO-220AB (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- 175°C Operating Temperature
- Avalanche Rated
- Low $R_{DS(on)}$
- Fast Intrinsic Rectifier
- High Current Handling Capability

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Rectification
- DC/DC Converters and Off-Line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	120		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 100\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 150^\circ\text{C}$			5 μA
				175 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5 \cdot I_{D25}, \text{Notes 1, 2}$			17 m Ω

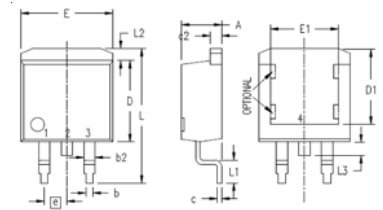
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	36	60	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		4740	pF
C_{oss}			415	pF
C_{rss}			66	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		21	ns
t_r			14	ns
$t_{d(off)}$			39	ns
t_f			28	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		80	nC
Q_{gs}			23	nC
Q_{gd}			20	nC
R_{thJC}	TO-220	0.50	0.46 $^\circ\text{C/W}$	
R_{thCH}			$^\circ\text{C/W}$	

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			80 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			320 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 0.5 \cdot I_{D25}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 60\text{V}$		90	ns
I_{RM}			4	A
Q_{RM}			180	nC

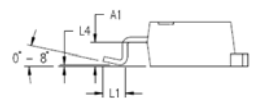
Notes: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

TO-263 Outline



Pins:

1 - Gate
2,4 - Drain
3 - Source



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 Outline

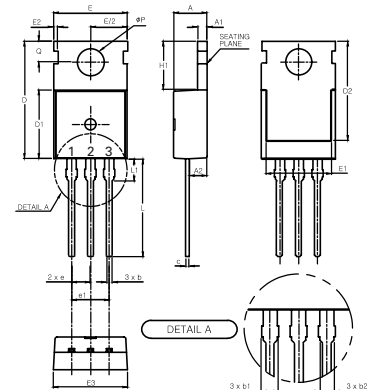


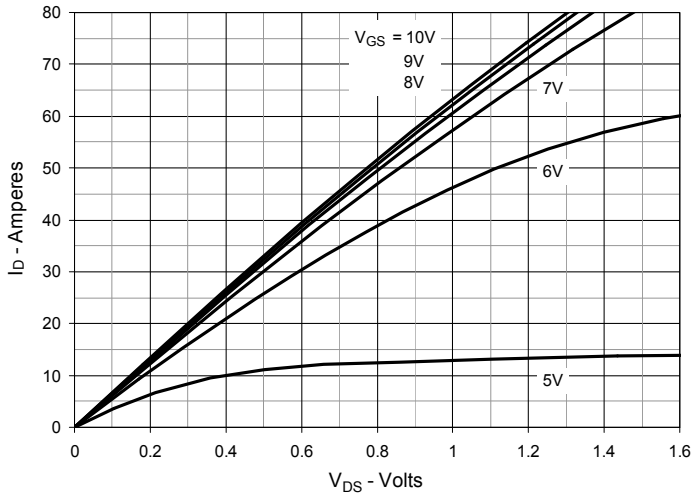
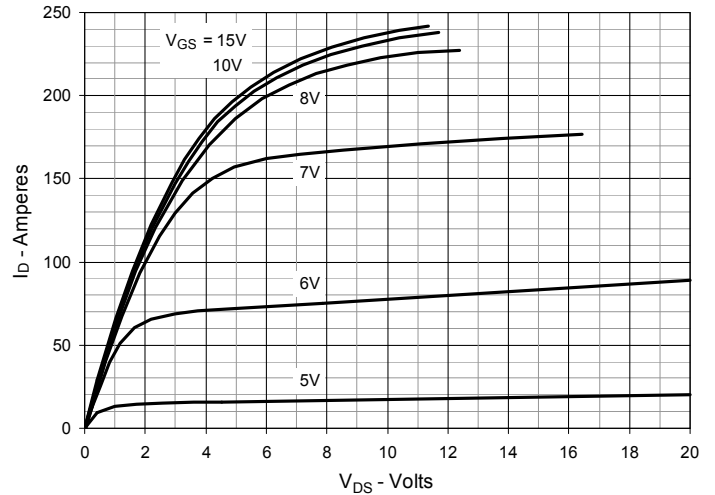
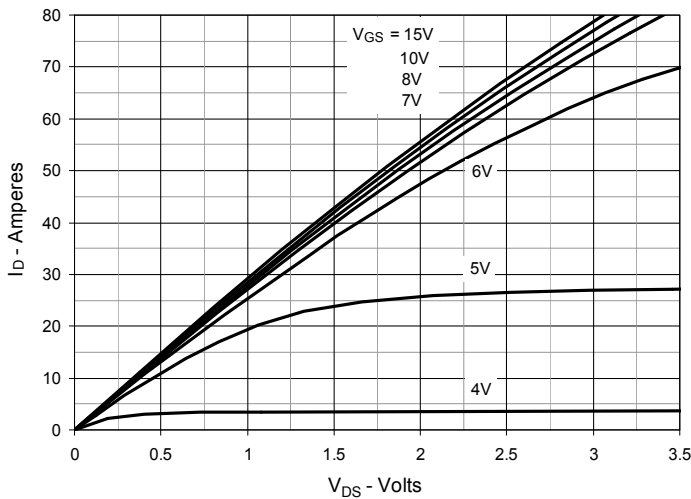
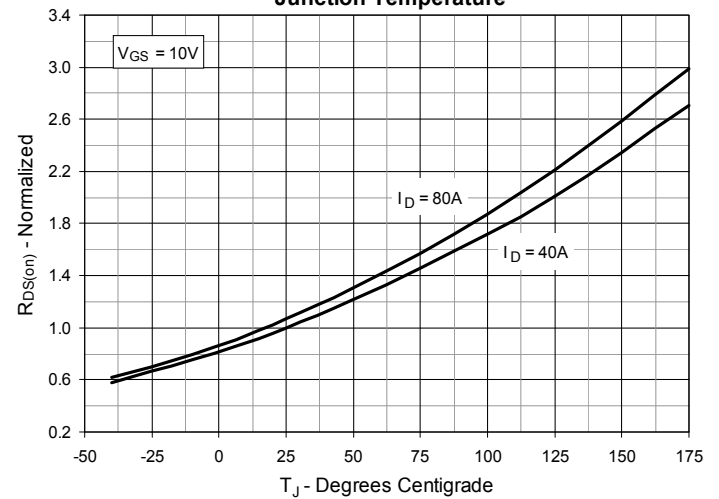
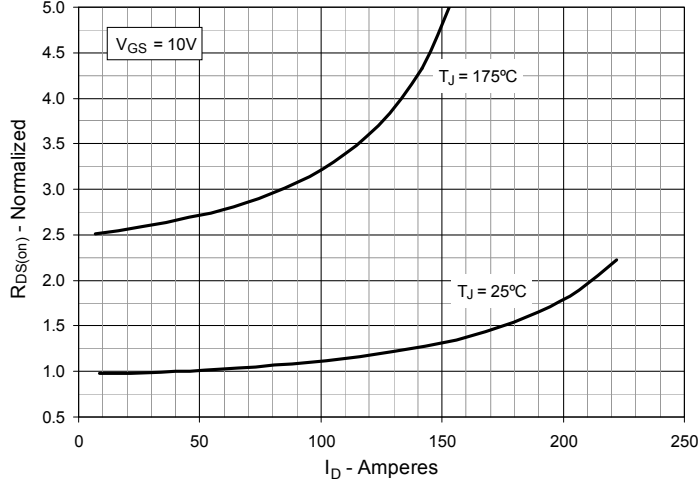
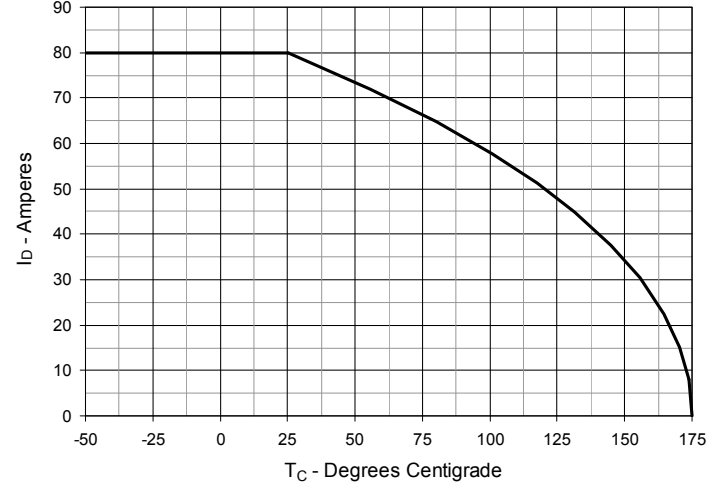
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Drain Current

Fig. 6. Drain Current vs. Case Temperature


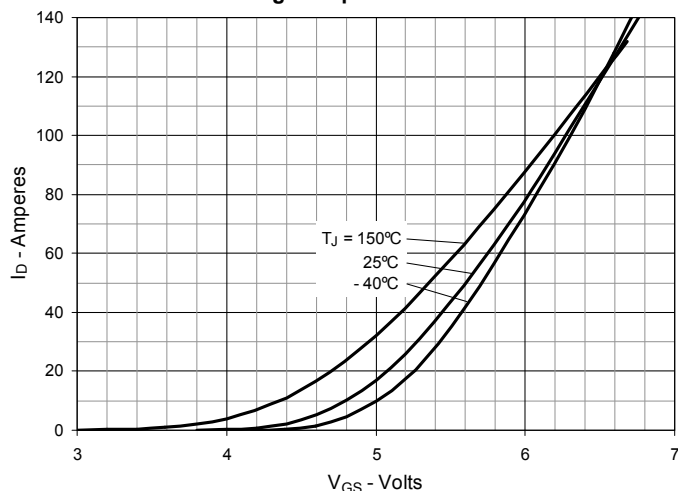
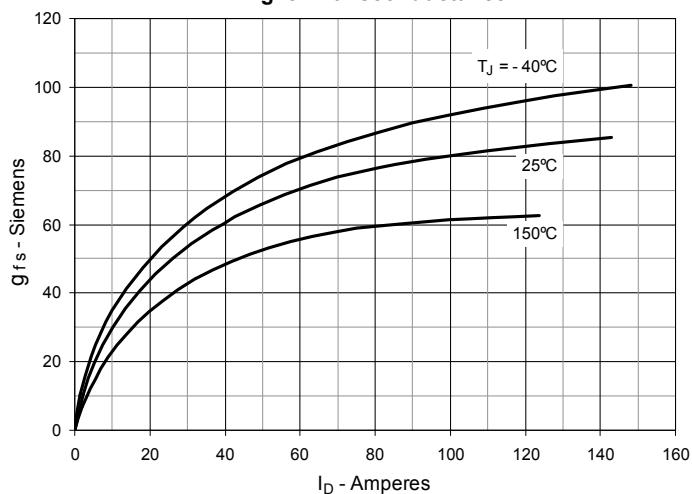
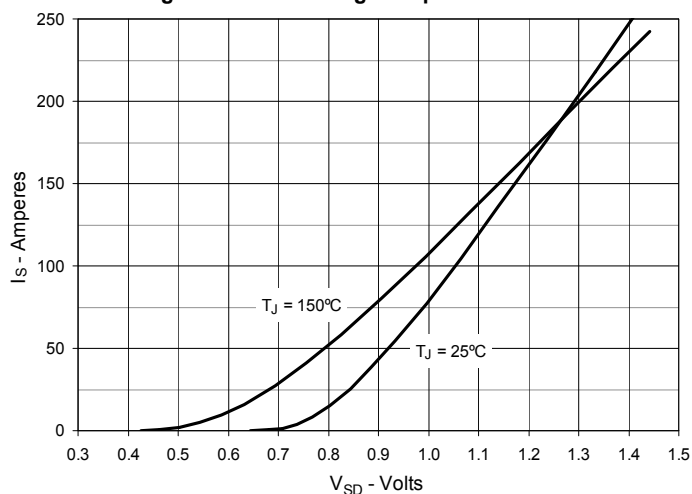
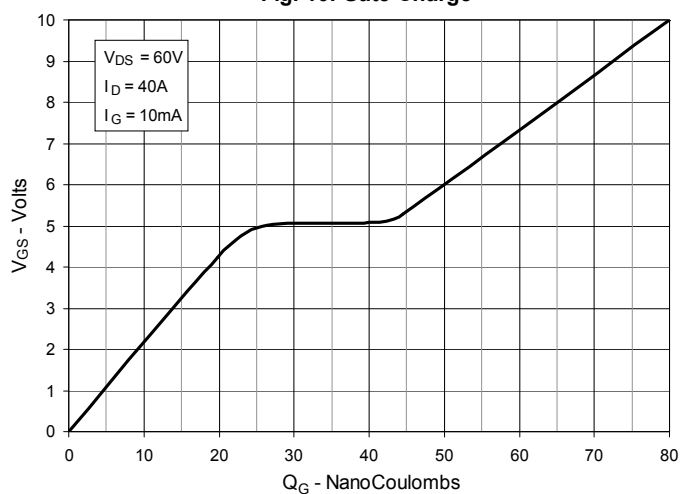
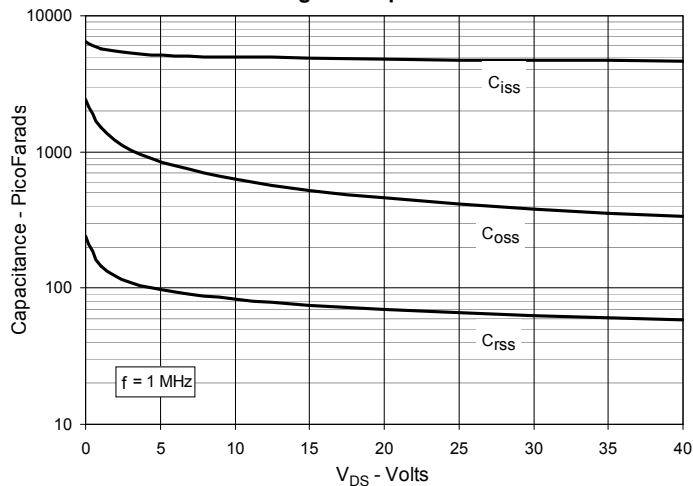
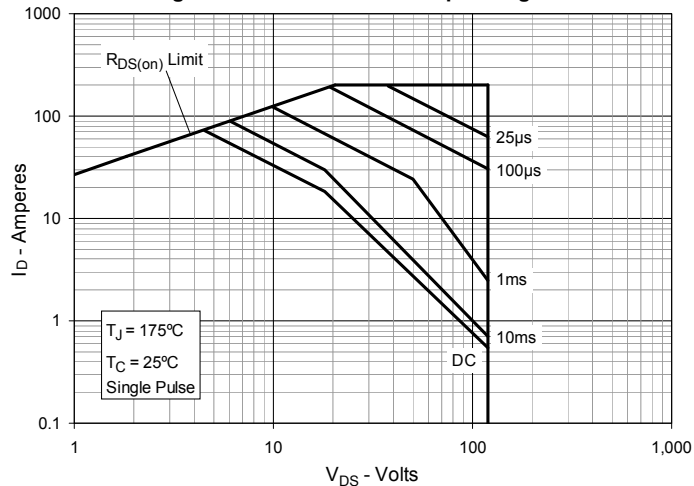
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

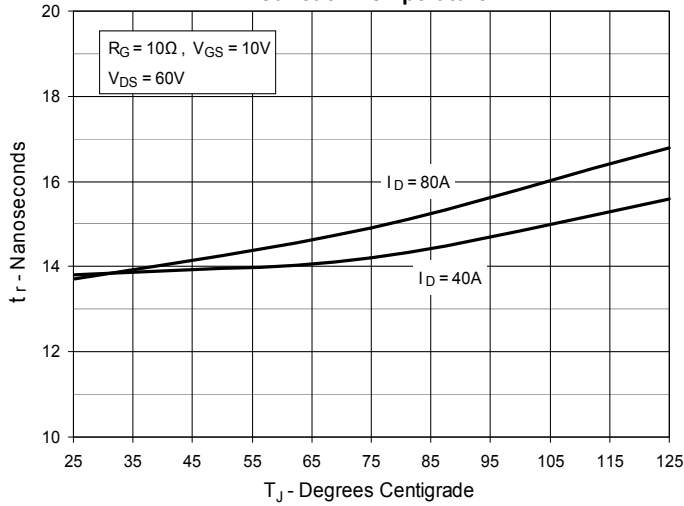


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

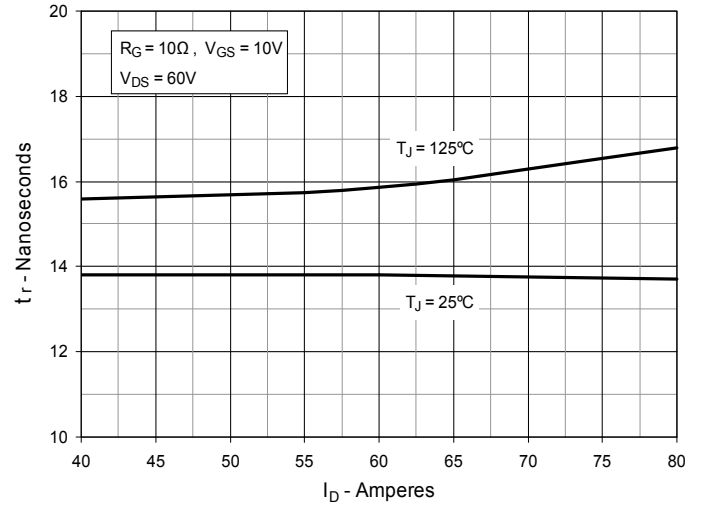


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

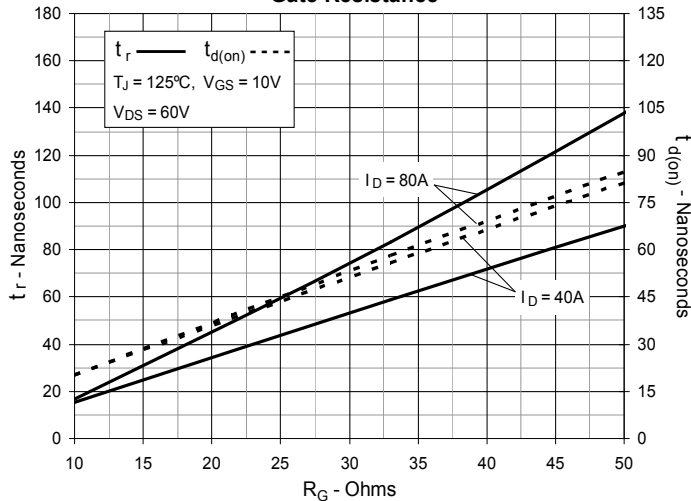


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

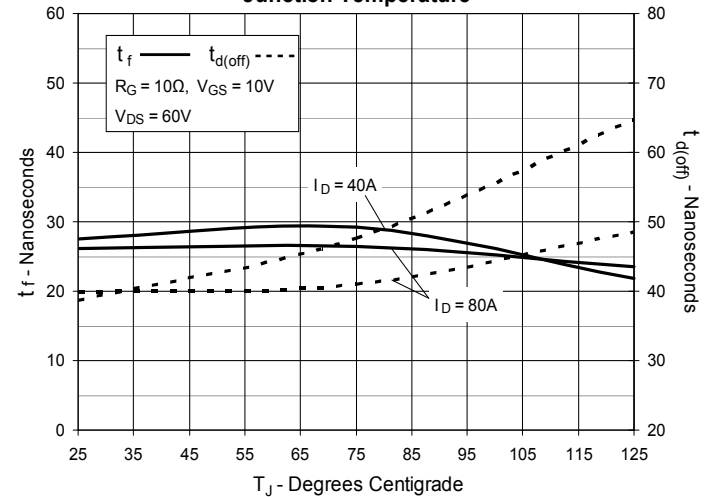


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

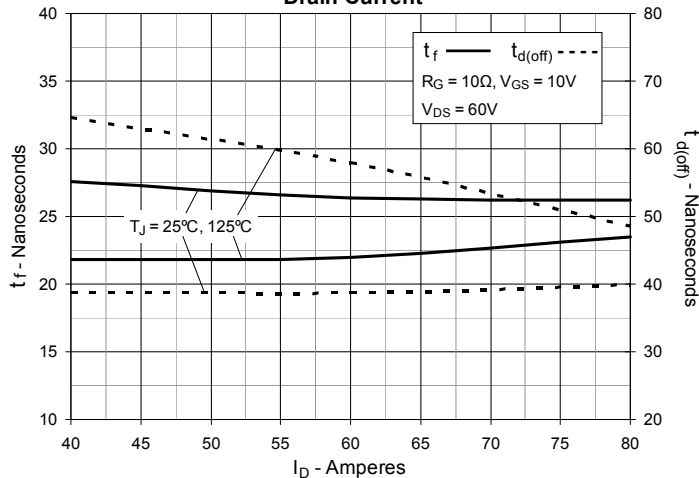


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

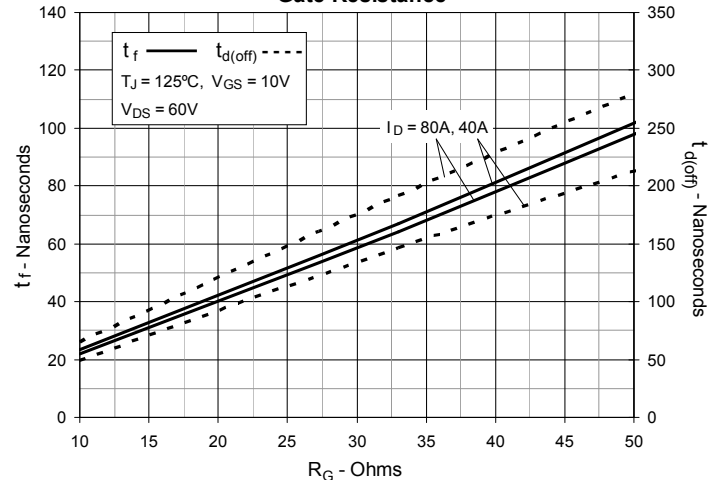


Fig. 19. Maximum Transient Thermal Impedance

